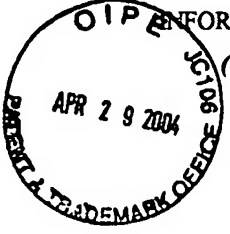


Date: April 27, 2004

Page 1 of 3

U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)				ATTY. DOCKET NO. BU-021AX		APPLICATION NO. 10/790,403	
				APPLICANT: M. Selim Unlu et al.			
				FILING DATE March 1, 2004		TC ART UNIT	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	PUBLICATION/ ISSUE DATE	NAME	CLASS	SUBCLASS	FILING DATE	
MW	US 5,770,511	06/23/1998	Matsumoto et al	438	406		
MW	US 5,376,215	12/27/1994	Ohta et al	156	345		
MW	US 4,670,765	06/02/1987	Nakamura et al	357	30		
MW	US 5,757,986	05/26/1998	Crampton et al	385	2		
MW	US 5,767,507	06/16/1998	Unlu et al	250	225		
MW	US 5,710,057	01/20/1998	Kenney	437	62		
MW	US 5,671,914	09/30/1997	Kalkhoran et al	257	77		
FOREIGN PATENT DOCUMENTS							
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO	
OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, etc.)							
MW	Ishikawa et al., "Epitaxy-ready Si/SiO ₂ Bragg Reflectors by Multiple Separation-by-Implanted Oxygen", Appl. Phys. Letters, Vol 69, No. 25 16 December 1996.						
MW	Sinnis et al. "Silicon-based Resonant-cavity-enhanced Photodiode with a Buried SiO ₂ Reflector", Appl. Phys. Letters, Vol 74, No. 9, 1 March 1999.						
MW	Schow et al., "Design and Implementation of High-speed Planar Si Photodiodes Fabricated on SOI Substrates", IEEE Journal of Quantum Electronics, Vol. 35, No. 10, October 1999.						
MW	Schaub et al., "Resonant-cavity-enhanced High-speed Si Photodiode Grown by Epitaxial Lateral Overgrowth", IEEE Photonics Technology Letters, Vol. 11, No. 12, 12 December 1999.						
MW	Jalali et al., "Advances in Silicon-on-Insulator Optoelectronics", IEEE Journal of Selected Topics in Quantum Electronics, Col. 4, No. 6, Nov/Dec 1998.						
MW	Fukatsu et al., "Spectral Modulation of Luminescence of Strained Si _{1-x} Ge _x /Si Quantum Wells in a Vertical Cavity with air/Si and Si/SiO ₂ Interface Mirrors", Appl. Phys. Letters, Vol. 65, No. 24, 12 December 1994.						
EXAMINER MW/iczewski				DATE CONSIDERED 02/2006			
*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Date: April 27, 2004

Page 2 of 3

(REV. 05/03) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)	ATTY. DOCKET NO. BU-021AX	APPLICATION NO. 10/790,403
	APPLICANT: M. Selim Unlu et al.	
	FILING DATE March 1, 2004	TC ART UNIT

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	PUBLICATION/ ISSUE DATE	NAME	CLASS	SUBCLASS	FILING DATE
<i>MW</i>	US 5,726,440	03/10/1998	Kalkhoran et al	250	214.1	
<i>MW</i>	US 5,498,863	03/12/1996	Miller	250	214.1	
<i>MW</i>	US 5,389,797	02/14/1995	Bryan et al	257	21	
<i>MW</i>	US 5,455,421	10/03/1995	Spears	250	338.4	
<i>MW</i>	US 5,020,066	05/28/1991	Iga et al	372	45	
<i>MW</i>	US 5,559,912	09/24/1996	Agahi et al	385	42	
<i>MW</i>	US 5,525,828	06/11/1996	Bassous et al	257	457	
<i>MW</i>	US 5,793,060	08/11/1998	Morikawa	257	85	

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO

OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, etc.)

<i>MW</i>	Yonehara et al., "Epitaxial Layer Transfer by Bond and Etch Back of Porous Si", Appl Phys. Letters, Vol. 64, No. 16, 18 April 1994.
<i>MW</i>	Tan et al., "Modeling and Performance of Wafer-Fused Resonant-Cavity Enhanced Photodetectors", IEEE Journal of Quantum Electronics, Vol. 31, No. 10, 10 October 1995.
<i>MW</i>	Bean et al., "High-Speed Polysilicon Resonant-Cavity Photodiode with SiO ₂ -Si Bragg Reflectors", IEEE Photonics Technology Letters, Col. 9, No. 6, June 1997.
<i>MW</i>	Diaz et al., "Si/SiO ₂ Resonant Cavity Photodetector", Appl. Phys. Letters, Vol. 69, No. 19, 4 November 1996.
<i>MW</i>	Murtaza et al., "Short-Wavelength, High-Speed, Si-Based Resonant-Cavity Photodetector", IEEE Photonics Technology Letters, Vol. 8, No. 7, July 1996.
<i>MW</i>	Sato et al., "High-Quality Epitaxial Layer Transfer (ELTRAN) by Bond And Etch-Back of Porous Si", Proceedings of 1995 IEEE International SOI Conference, October 1995.

EXAMINER *MW/iczewski*DATE CONSIDERED *02/2006*

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Date: April 27, 2004

Page 3 of 3

(REV. 05/03) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)	ATTY. DOCKET NO. BU-021AX	APPLICATION NO. 10/790,403
	APPLICANT: M. Selim Unlu et al.	
	FILING DATE March 1, 2004	TCART UNIT

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	PUBLICATION/ ISSUE DATE	NAME	CLASS	SUBCLASS	FILING DATE
MW	US 5,837,561	11/17/98	Kish, Jr. et al.	438	47	
MW	US 5,374,564	12/20/94	Bruehl	437	24	
MW	US 5,227,648	7/13/93	Woo	257	185	
	US					
	US					
	US					
	US					

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, etc.)

MW	Alles et al., "Advanced Manufacturing of SIMOX for Low Power Electronics", Solid State Electronics, Vol. 39, No. 4, pp 499-504, 1996.
MW	Wada et al., "A New Approach of Photonic Bandgap Formation-Wafer Bonding and Delamination Technique", Extended Abstracts of the 1998 International Conference on Solid State Devices and Materials, pp 382-383 1998.
MW	Unlu et al., "Resonant Cavity Enhanced Photonic Devices", Journal Appl. Phys. Vol. 78, No. 2, 15 July 1995.

EXAMINER <i>MWilczewski</i>	DATE CONSIDERED <i>02/2006</i>
*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	